



High Speed Super Low Power SRAM

32K-Word By 8 Bit

CS18LV02560

■ DESCRIPTION

The CS18LV02560 is a high performance; high speed and super low power CMOS Static Random Access Memory organized as 32,768 words by 8bits and operates from a wide range of 2.2 to 5.5V supply voltage. Advanced CMOS technology and circuit techniques provide both high speed, super low power features and maximum access time of 55/70ns in 3.0V operation. Easy memory expansion is provided by an active LOW chip enable (/CE) and active LOW output enable (/OE).

The CS18LV02560 has an automatic power down feature, reducing the power consumption significantly when chip is deselected. The CS18LV02560 is available in JEDEC standard 28-pin TSOP I (8x13.4 mm), SOP (330 mil) and PDIP (600 mil) packages.

■ FEATURES

- Wide operation voltage : 2.2 ~ 5.5V
- Ultra low power consumption:
 - Vcc=3.0 Operating current 15ma(Max.) & CMOS standby current 0.2ua (Typ.)
 - Vcc=5.0 Operating current 20ma(Max.) & CMOS standby current 1.5ua (Typ.)
- High speed access time: 55~70ns.
- Automatic power down when chip is deselected.
- Three state outputs and TTL compatible.
- Data retention supply voltage as low as 1.5V.
- Easy expansion with /CE and /OE options.

■ PRODUCT FAMILY

Part No.	Operating Temp.	Vcc Range	Speed (ns)	Standby Current (Typ.) I _{CCSB1}	Package Type	
CS18LV02560AC	0~70°C	2.2~5.5V	55/70	1.5uA (Vcc = 5.0V)	28 SOP	
CS18LV02560BC					28 TSOP I	
CS18LV02560PC					28 PDIP	
CS18LV02560ZC					Dice	
CS18LV02560AI	-40~85°C		2.2~5.5V	55/70	0.2uA (Vcc= 3.0V)	28 SOP
CS18LV02560BI						28 TSOP I
CS18LV02560PI						28 PDIP
CS18LV02560ZI						Dice

Note: Green package part no, sees order information.

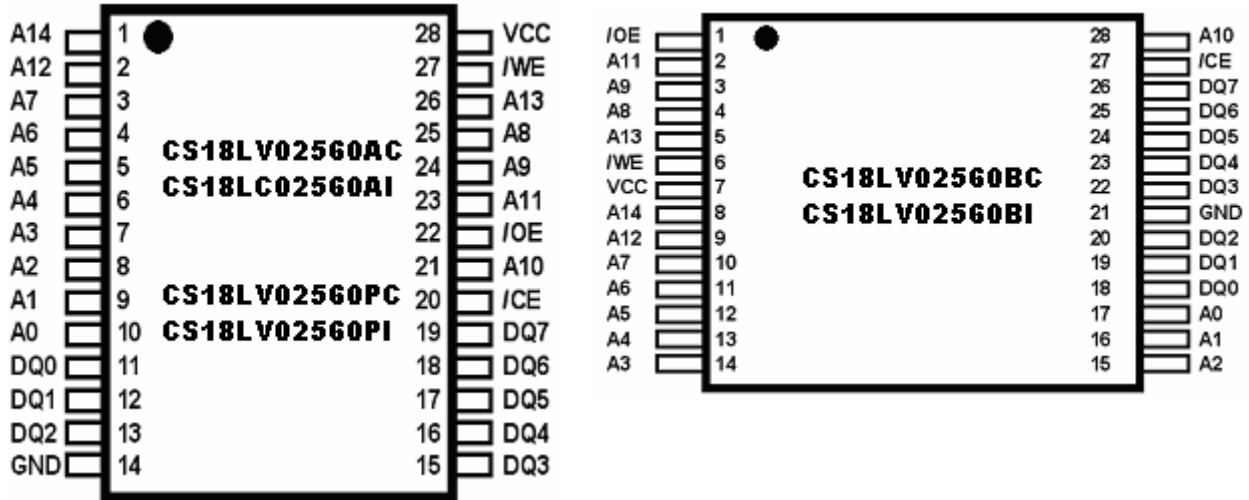


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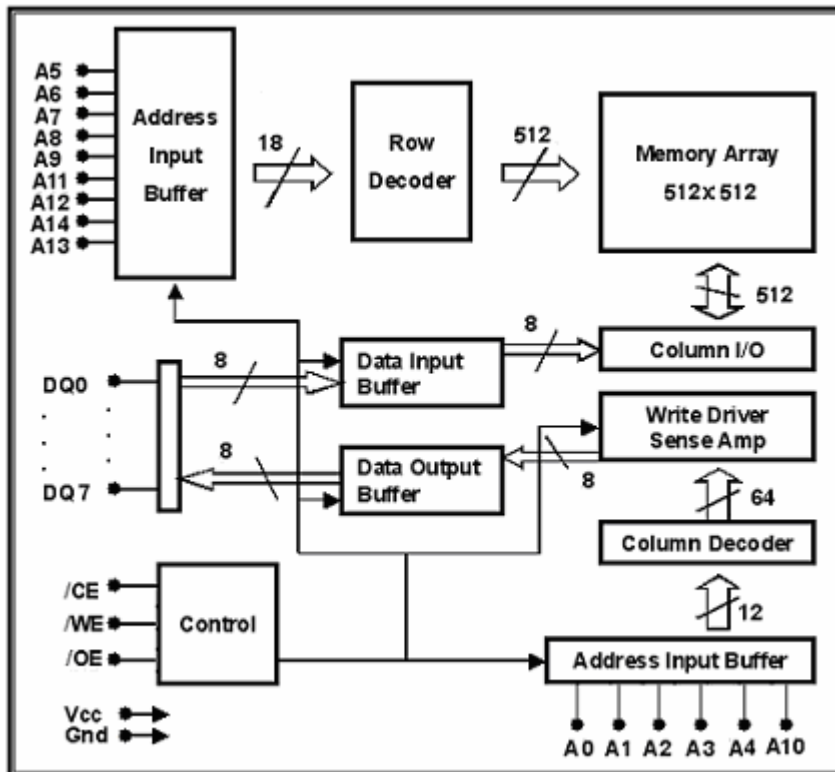
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PIN CONFIGURATIONS



BLOCK DIAGRAM





■ PIN DESCRIPTIONS

Name	Type	Function
A0 – A14	Input	Address inputs for selecting one of the 32,768 x 8 bit words in the RAM
/CE	Input	/CE is active LOW. Chip enable must be active when data read from or write to the device. If chip enable is not active, the device is deselected and in a standby power mode. The DQ pins will be in high impedance state when the device is deselected.
/WE	Input	The Write enable input is active LOW. It controls read and write operations. With the chip selected, when /WE is HIGH and /OE is LOW, output data will be present on the DQ pins, when /WE is LOW, the data present on the DQ pins will be written into the selected memory location.
/OE	Input	The output enable input is active LOW. If the output enable is active while the chip is selected and the write enable is inactive, data will be present on the DQ pins and they will be enabled. The DQ pins will be in the high impedance state when /OE is inactive.
DQ0~DQ7	I/O	These 8 bi-directional ports are used to read data from or write data into the RAM.
Vcc	Power	Power Supply
Gnd	Power	Ground

■ TRUTH TABLE

Mode	/WE	/CE	/OE	I/O state	Vcc Current
Not Selected	X	H	X	High Z	I_{SB}, I_{SB1}
Output Disabled	H	L	H	High Z	I_{CC}
Read	H	L	L	D_{OUT}	I_{CC}
Write	L	L	X	D_{IN}	I_{CC}



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■ ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Rating	Unit
V _{TERM}	Terminal Voltage with Respect to GND	-0.5 to V _{CC} +0.5	V
T _{BIAS}	Temperature Under Bias	-40 to +125	°C
T _{STG}	Storage Temperature	-60 to +150	°C
P _T	Power Dissipation	1.0	W
I _{OUT}	DC Output Current	20	mA

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

■ OPERATING RANGE

Range	Ambient Temperature	V _{CC}
Commercial	0~70°C	2.2 ~ 5.5V
Industrial	-40~85°C	2.2 ~ 5.5V

■ CAPACITANCE⁽¹⁾(T_A=25°C, f=1.0MHz)

Symbol	Parameter	Conduction	MAX.	Unit
C _{IN}	Input Capacitance	V _{IN} =0V	6	pF
C _{DQ}	Input/Output Capacitance	V _D I/O=0V	8	pF

1. This parameter is guaranteed, and not 100% tested.



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■ DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Name	Parameter	Test Condition	MIN	TYP ⁽¹⁾	MAX	Unit	
V_{IL}	Guaranteed Input Low Voltage ⁽²⁾	V _{CC} =3.0V	-1.0		1.2	v	
		V _{CC} =5.0V			1.5		
V_{IH}	Guaranteed Input High Voltage ⁽²⁾	V _{CC} =3.0V	2.0		V _{CC} +0.2	v	
		V _{CC} =5.0V	2.5				
I_{IL}	Input Leakage Current	V _{CC} =MAX, V _{IN} =0 to V _{CC}			1	uA	
I_{OL}	Output Leakage Current	V _{CC} =MAX, /CE=V _{IN} , or /OE=V _{IN} , V _{IO} =0V to V _{CC}			1	uA	
V_{OL}	Output Low Voltage	V _{CC} =MAX, I _{OL} = 1mA			0.4	v	
V_{OH}	Output High Voltage	V _{CC} =MIN, I _{OH} = -1mA	2.2			v	
I_{CC}	Operating Power Supply Current	/CE=V _{IL} , I _{DQ} =0mA, F=F _{MAX} =1/ t _{RC}	V _{CC} =3.0V			15	mA
			V _{CC} =5.0V			20	
I_{CCSB}	TTL Standby Supply	/CE=V _{IH} , I _{DQ} =0mA,			0.5	mA	
I_{CCSB1}	CMOS Standby Current	/CE ≥ V _{CC} -0.2V, V _{IN} ≥ V _{CC} -0.2V or V _{IN} ≤ 0.2V,	V _{CC} =3.0V			0.2	uA
			V _{CC} =5.0V			1.5	

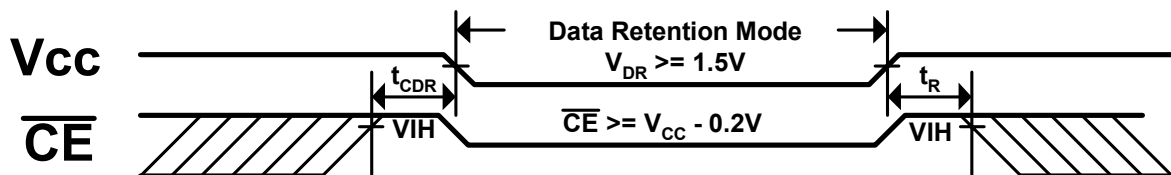
1. Typical characteristics are at TA = 25°C.
2. These are absolute values with respect to device ground and all overshoots due to system or tester notice are included.
3. V_{CC} operating range at 3V: 2.7v ~ 3.3v
4. V_{CC} operating range at 5V: 4.5v ~ 5.5v

■ DATA RETENTION CHARACTERISTICS (Over Operating Range)

Name	Parameter	Test Condition	MIN	TYP ⁽¹⁾	MAX	Unit
V_{DR}	V_{CC} for Data Retention	$/CE \geq V_{CC}-0.2V, V_{IN} \geq V_{CC}-0.2V$ or $V_{IN} \leq 0.2V$	1.5			V
I_{CCDR}	Data Retention Current	$/CE \geq V_{CC}-0.2V, V_{IN} \geq V_{CC}-0.2V$ or $V_{IN} \leq 0.2V$		0.2	2	μA
		$V_{CC}=3.0V$		1.0	4	
T_{CDR}	Chip Deselect to Data Retention Time	Refer to Retention Waveform	0			ns
t_R	Operation Recovery Time		t_{RC} (2)			ns

1. $T_A = 25^\circ C$
2. t_{RC} = Read Cycle Time.
3. V_{CC} operating range at 3V: 2.7v ~ 3.3v
4. V_{CC} operating range at 5V: 4.5v ~ 5.5v

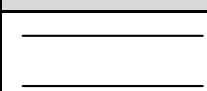

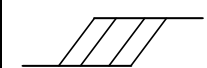
■ LOW V_{CC} DATA RETENTION WAVEFORM (/CE Controlled)



■ AC TEST CONDITIONS

Input Pulse Levels	$V_{CC}/0V$
Input Rise and Fall Times	5ns
Input and Output Timing Reference Level	$0.5V_{CC}$
Output Load	See FIGURE 1A and 1B

■ KEY TO SWITCHING WAVEFORMS

WAVEFORMS	INPUTS	OUTPUTS
	MUST BE STEADY	MUST BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGE FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGE FROM L TO H

	DON'T CARE ANY CHANGE PERMITTED	CHANGE STATE UNKNOWN
	DOES NOT APPLY	CENTER LINE IS HIGH IMPEDANCE OFF STATE

AC TEST LOADS AND WAVEFORMS

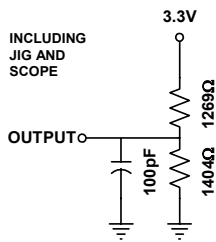


FIGURE 1A

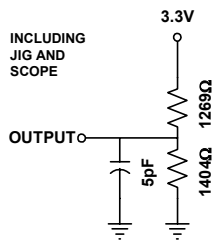
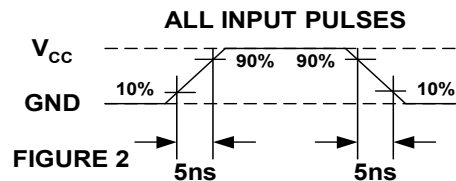


FIGURE 1B



AC ELECTRICAL CHARACTERISTICS (Over Operating Range)

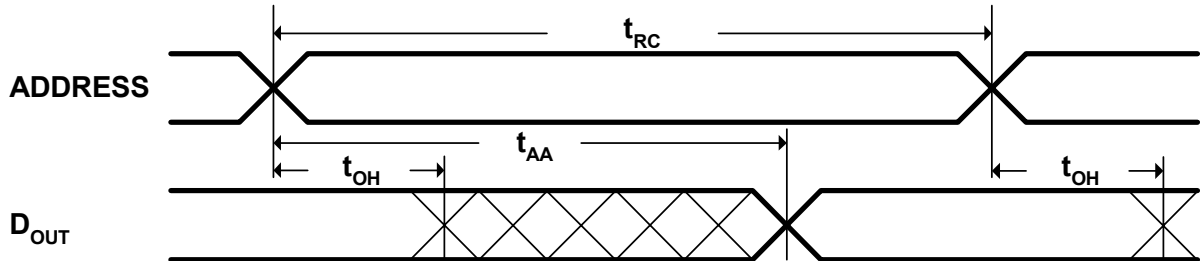
< READ CYCLE >

JEDEC Name	Symbol	Description	-55		-70		Unit
			MIN	MAX	MIN	MAX	
t _{AVAX}	t _{RC}	Read Cycle Time	55		70		ns
t _{AVQV}	t _{AA}	Address Access Time		55		70	ns
t _{ELQV}	t _{CE}	Chip Select Access Time		55		70	ns
t _{GLQV}	t _{OE}	Output Enable to Output Valid		30		50	ns
t _{ELQX}	t _{CLZ} ⁽⁵⁾	Chip Select to Output Low Z	10		10		ns
t _{GLQX}	t _{OLZ} ⁽⁵⁾	Output Enable to Output in Low Z	5		5		ns
t _{EHQZ}	t _{CHZ} ⁽⁵⁾	Chip Deselect to Output in High Z	0	35	0	35	ns
t _{GHQZ}	t _{OHZ} ⁽⁵⁾	Output Disable to Output in High Z	0	30	0	30	ns
t _{AXOX}	t _{OH}	Address Change to Out Disable	10		10		ns

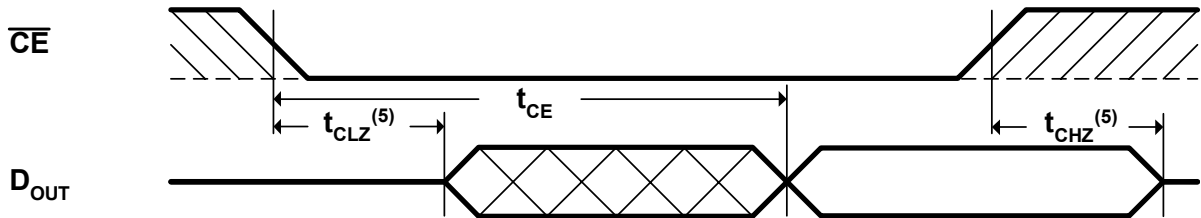


SWITCHING WAVEFORMS (READ CYCLE)

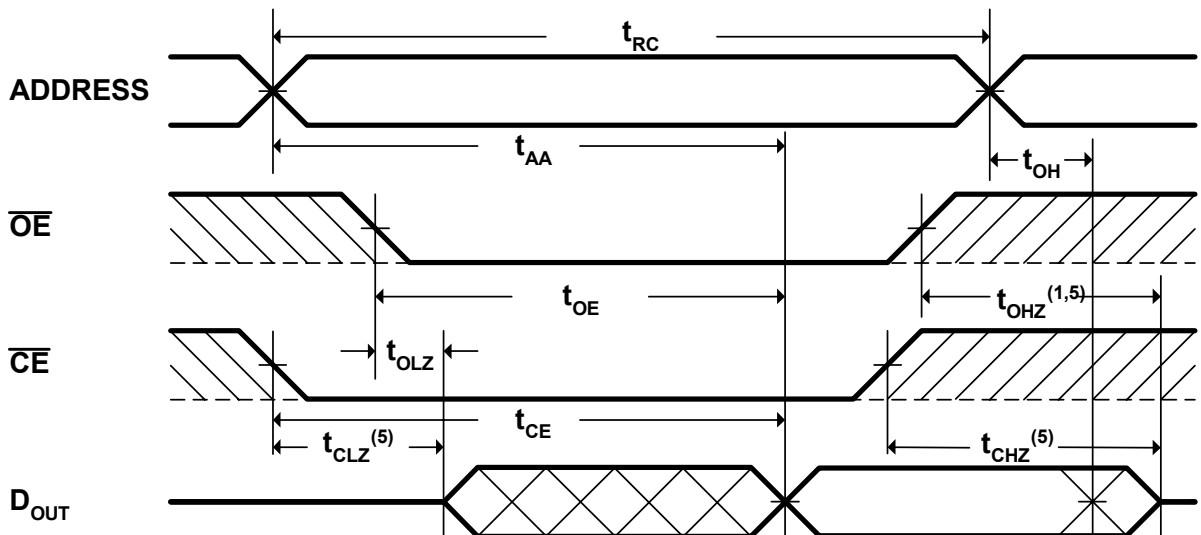
READ CYCLE1 (1,2,4)



READ CYCLE2 (1,3,4)



READ CYCLE3 (1,4)



**NOTES:**

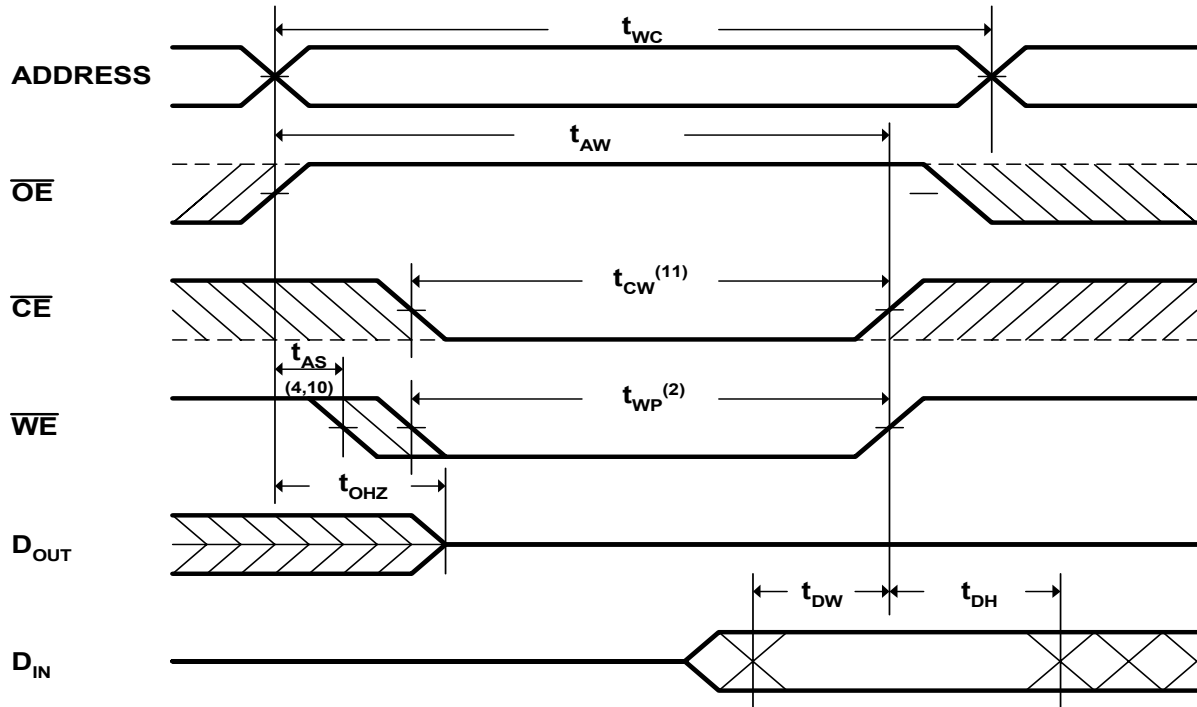
1. /WE is high in read Cycle.
2. Device is continuously selected when /CE = V_{IL}.
3. Address valid prior to or coincident with CE transition low.
4. /OE = V_{IL}.
5. Test conditions assume signal transition times of 5ns or less, timing reference levels of 0.5V_{CC}, input pulse levels of 0V to V_{CC} and output loading specified in Figure 1A.
6. Transition is measured ±500mV from steady state with C_L = 5pF as shown in Figure 1B. The parameter is guaranteed but not 100% tested.

■ AC ELECTRICAL CHARACTERISTICS (Over Operating Range)**< WRITE CYCLE >**

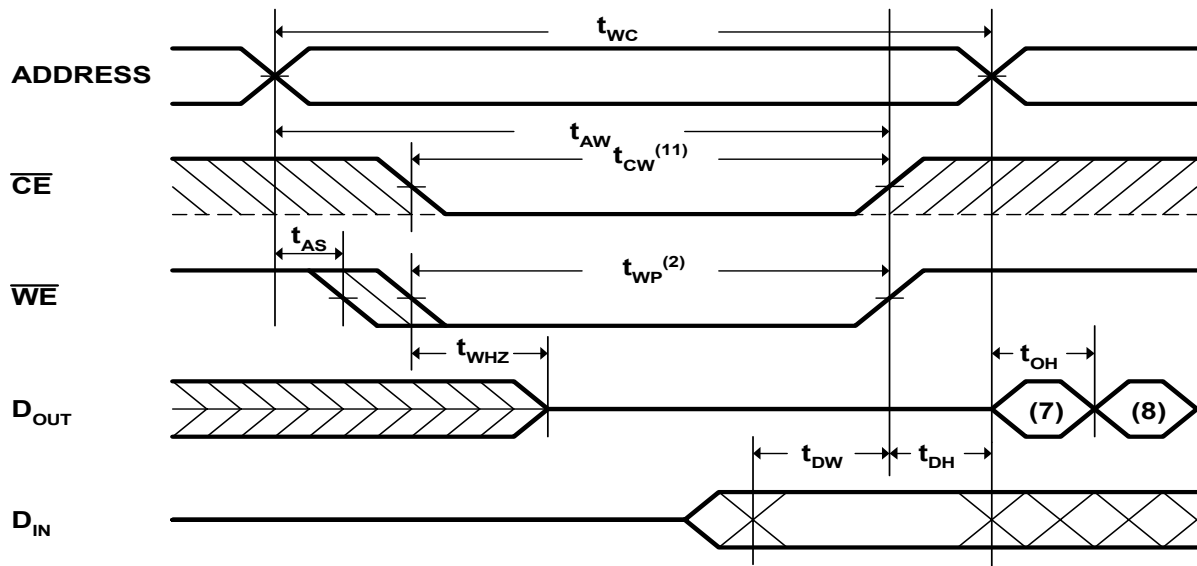
JEDEC Name	Symbol	Description	-55		-70		Unit
			MIN	MAX	MIN	MAX	
t _{AVAX}	t _{wc}	Write Cycle Time	55		70		ns
t _{E1LWH}	t _{cw}	Chip Select to End of Write	55		70		ns
t _{AVWL}	t _{AS}	Address Setup Time	0		0		ns
t _{AVWH}	t _{AW}	Address Valid to End of Write	55		70		ns
t _{WLWH}	t _{wP}	Write Pulse Width	40		50		ns
t _{WHAX}	t _{wR}	Write Recovery Time	0		0		ns
t _{WLQZ}	t _{WHZ} ⁽¹⁰⁾	Write to Output in High Z		25		35	ns
t _{DVWH}	t _{DW}	Data to Write Time Overlap	20		30		ns
t _{WHDX}	t _{DH}	Data Hold for Write End	0		0		ns
t _{GHQZ}	t _{OHZ} ⁽¹⁰⁾	Output Disable to Output in High Z	0	30	0	30	ns
t _{WHOX}	t _{OW} ⁽¹⁰⁾	End of Write to Output Active	5		5		ns

SWITCHING WAVEFORMS (WRITE CYCLE)

WRITE CYCLE1⁽¹⁾



WRITE CYCLE2^(1,6)





NOTES:

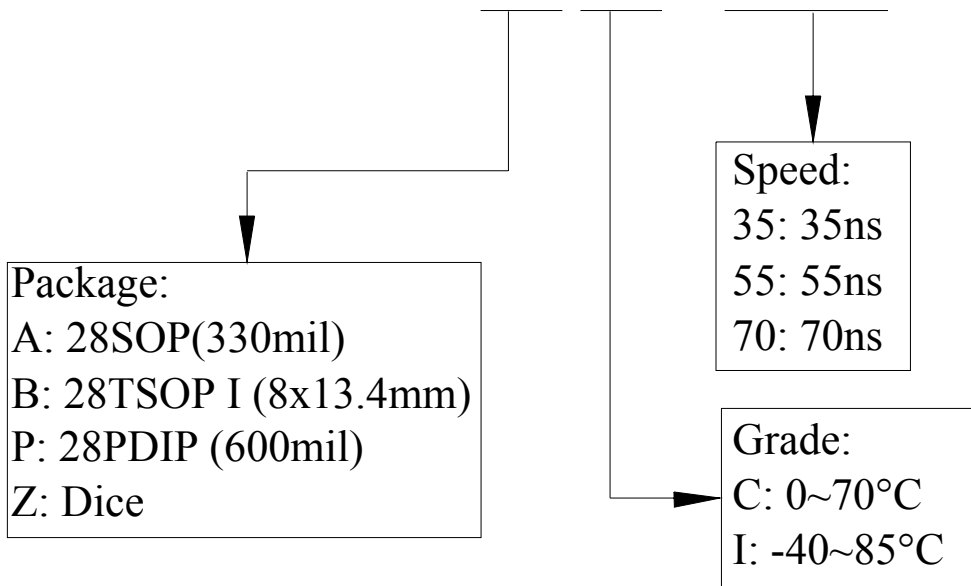
1. /WE must be high during address transitions.
2. The internal write time of the memory is defined by the overlap of /CE and /WE low. All signals must be active to initiate a write and any one signal can terminate a write by going inactive. The data input setup and hold timing should be referenced to the second transition edge of the signal that terminates the write.
3. T_{WR} is measured from the earlier of /CE or /WE going high at the end of write cycle.
4. During this period, DQ pins are in the output state so that the input signals of opposite phase to the outputs must not be applied.
5. If the /CE low transition occurs simultaneously with the /WE low transitions or after the /WE transition, output remain in a high impedance state.
6. /OE is continuously low ($/OE = V_{IL}$). D_{OUT} is the same phase of write data of this write cycle.
8. D_{OUT} is the read data of next address.
9. If /CE is low during this period, DQ pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.
10. Test conditions assume signal transition times of 5ns or less, timing reference levels of 0.5VCC, input pulse levels of 0V to VCC and output loading specified in Figure 1A.
11. Transition is measured $\pm 500\text{mV}$ from steady state with $C_L = 5\text{pF}$ as shown in Figure 1B. The parameter is guaranteed but not 100% tested.
12. T_{CW} is measured from the later of /CE going low to the end of write.



ORDER INFORMATION

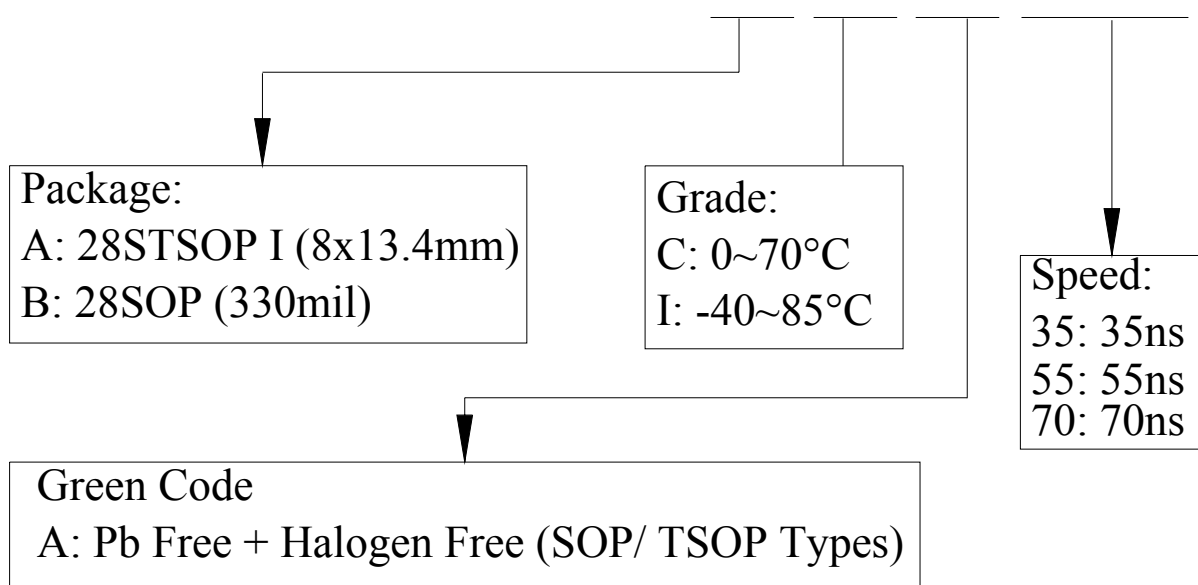
1. NON-GREEN PACKAGE:

CS18LV02560 X X - XX



2. GREEN PACKAGE:

CS18LV02560 X X X XX





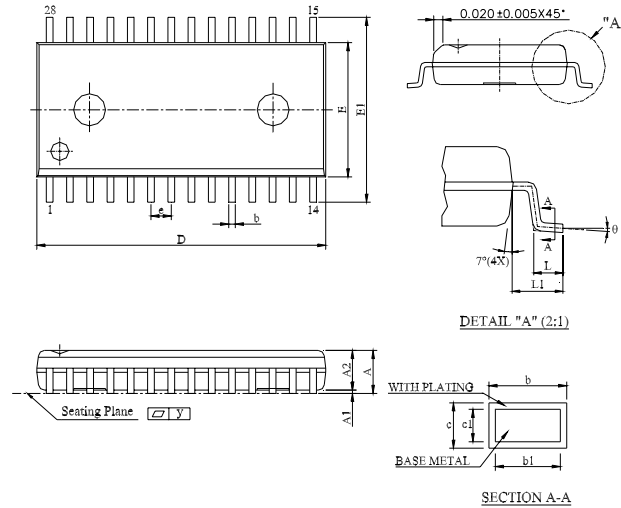
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PACKAGE DIMENSIONS

- 28 pin SOP (330 mil) :



SYMBOL UNIT	A	A1	A2	b	b1	c	c1	D	E	E1	e	L	L1	y	Ø
	mm	Min. 2.540 Nom. 2.692 Max. 2.844	0.102 0.226 0.350	2.362 2.489 2.616	0.35 — 0.50	0.35 — 0.45	0.20 — 0.32	0.20 — 0.28	17.983 18.110 18.237	8.280 8.407 8.534	11.506 11.811 12.116	1.118 1.270 1.422	0.700 0.964 1.228	1.520 1.720 1.920	— — 0.1
inch	Min. 0.100 Nom. 0.106 Max. 0.112	0.004 0.009 0.014	0.093 0.098 0.103	0.014 — 0.020	0.014 — 0.018	0.008 — 0.012	0.008 — 0.011	0.708 0.713 0.718	0.326 0.331 0.336	0.453 0.465 0.477	0.044 0.050 0.056	0.0276 0.0380 0.0484	0.0598 0.0677 0.0756	— — 0.004	0° — 10°

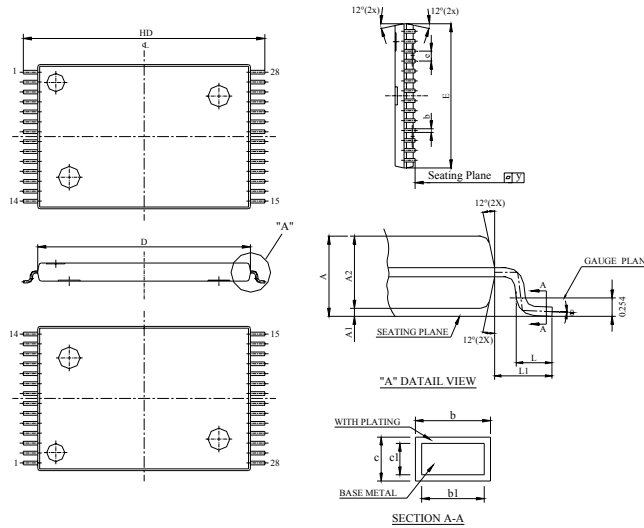


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- 28 pin TSOP I (8x13.4 mm) :



SYMBOL		A	A1	A2	b	b1	c	c1	D	E	e	HD	L	L1	y	Ø
mm	Min.	1.00	0.050	0.95	0.17	0.17	0.10	0.10	11.70	7.90	0.45	13.20	0.40	0.70	-	0°
	Norm.	1.10	0.115	1.00	0.22	0.20	-	-	11.80	8.00	0.55	13.40	0.50	0.80	-	-
	Max.	1.20	0.180	1.05	0.27	0.23	0.21	0.16	11.90	8.10	0.65	13.60	0.70	0.90	0.1	8°
inch	Min.	0.0393	0.0019	0.037	0.007	0.007	0.004	0.004	0.461	0.311	0.018	0.520	0.0157	0.0275	-	0°
	Norm.	0.0433	0.0045	0.039	0.009	0.008	-	-	0.465	0.315	0.022	0.528	0.0197	0.0315	-	-
	Max.	0.0473	0.0071	0.041	0.011	0.009	0.008	0.006	0.469	0.319	0.026	0.536	0.0277	0.0355	0.004	8°

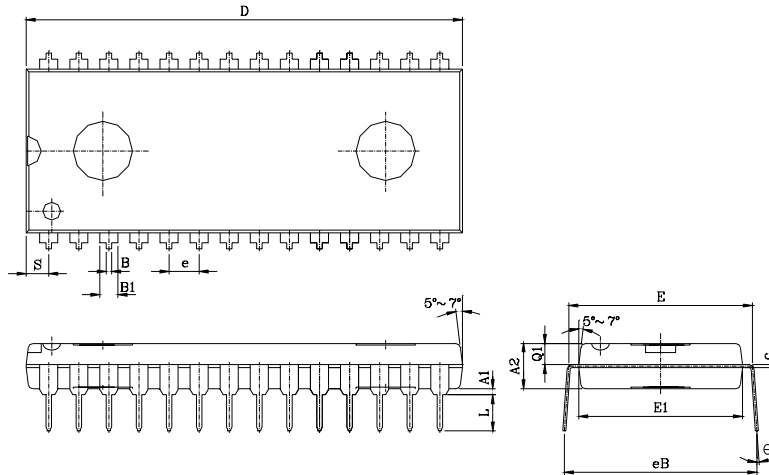


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- 28 pin PDIP (600mil):



SYMBOL		A1	A2	B	B1	c	D	E	E1	e	eB	L	S	Q1	θ
UNIT															
mm	Min.	0.254	3.683	0.330	1.270	0.152	36.957	14.986	13.716	2.540 (TYP)	15.748	3.048	1.778	1.651	3°
	Nom.	-	3.810	0.457	1.524	0.254	37.084	15.240	13.818		16.256	3.302	2.032	1.778	6°
	Max.	-	3.937	0.584	1.778	0.356	37.211	15.494	13.920		16.764	3.556	2.286	1.905	9°
inch	Min.	0.010	0.145	0.013	0.050	0.006	1.455	0.590	0.540	0.100 (TYP)	0.620	0.120	0.070	0.065	3°
	Nom.	-	0.150	0.018	0.060	0.010	1.460	0.600	0.544		0.640	0.130	0.080	0.070	6°
	Max.	-	0.155	0.023	0.070	0.014	1.465	0.610	0.548		0.660	0.140	0.090	0.075	9°